Refine Search

Search Results -

Terms	Documents
L12	0

Database:

```
US Pre-Grant Publication Full-Text Database
US Patents Full-Text Database
US OCR Full-Text Database
EPO Abstracts Database
JPO Abstracts Database
Derwent World Patents Index
IBM Technical Disclosure Bulletins
```

Search: L13

[Refine Search]

[Recall Text ⇕]   [Clear]   [Interrupt]

Search History

DATE: Tuesday, June 22, 2004   Printable Copy   Create Case

Set Name Query	Hit Count	Set Name
side by side		result set
DB=TDBD; PLUR=YES; OP=OR		
L13 L12	0	L13
DB=DWPI; PLUR=YES; OP=OR		
L12 L11	0	L12
DB=JPAB; PLUR=YES; OP=OR		
L11 L10	0	L11
DB=EPAB; PLUR=YES; OP=OR		
L10 L9	0	L10
DB=USOC; PLUR=YES; OP=OR		
L9 L8	0	L9
DB=PGPB; PLUR=YES; OP=OR		
L8 L7	0	L8
DB=USPT; PLUR=YES; OP=OR		
L7 L5 and "storage near5 transistor"	0	L7
L6 L5 and "sense transistor" and "read transistor" and "write transistor"	0	L6

h   e b   b   cg b   e e ch

L5	"memory cells" same ("common storage" or "common capacitor")	108	L5
L4	"memory eclls" same "common capacitor"	0	L4
L3	"memory eclls" same "common storage"	0	L3
L2	L1 "memory eclls" same (common near6 storage)	0	L2
L1	"memory eclls" same "common storage"	0	L1

END OF SEARCH HISTORY

h   e   b   b   cg   b   e   e   ch

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h   e b   b   cg b   e e ch

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h   e   b   b   cg b   e e ch